

Compound Semiconductor Materials North America TC Chapter

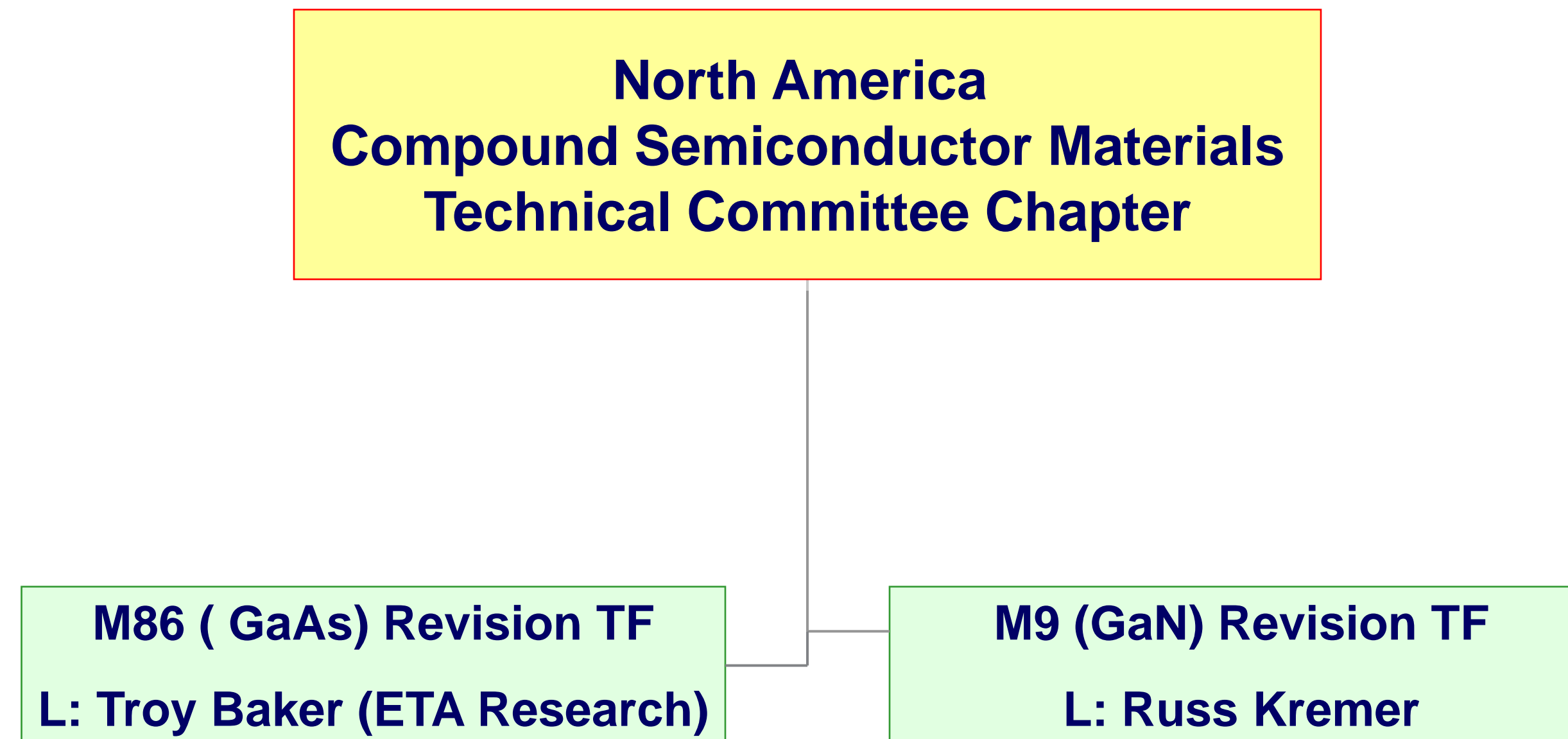
Liaison Report

June 2, 2021

Leadership

- Committee Co-chairs
 - Russ Kremer / Consultant
 - Jim Oliver / Consultant

Current Committee Structure



Meeting Information

- Last meeting
 - May 19, 2021
 - Online
- Next meeting
 - Nov 10, 2021
 - 9:00 AM – 11:00 AM Pacific
 - Online

Ballot Review

- Doc. 6735, Withdrawal of SEMI M42 - Specification for Compound Semiconductor Epitaxial Wafers
 - Passed as balloted
- Doc. 6736, Reapproval of SEMI M86 - Specification for Polished Monocrystalline c-Plane Gallium Nitride Wafers
 - Failed

New TFOFs and SNARFs



- M9 (GaAs) Revision TF
 - Doc. 6805, Revision of SEMI M9.5 with title change from “Specification for Round 100mm Polished Monocrystalline Gallium Arsenide Wafers for Electronic Device Applications” to “Specification for Round 100mm Polished Monocrystalline Gallium Arsenide Wafers
 - Doc. 6818, Withdrawal of SEMI M9.1-0813 — Specification For Round 50.8 mm Polished Monocrystalline Gallium Arsenide Wafers For Electronic Device Applications
 - Doc. 6819, Withdrawal of SEMI M9.6-0813 — Specification For Round 125 mm Diameter Polished Monocrystalline Gallium Arsenide Wafers
- M86 (GaN) Revision TF
 - Doc. 6806, Revision of M86, Specification for Polished Monocrystalline c-Plane Gallium Nitride Wafers

Authorized Ballot

- Cycle 5-2021

- Doc. 6805, Revision of SEMI M9.5 with title change from “Specification for Round 100mm Polished Monocrystalline Gallium Arsenide Wafers for Electronic Device Applications” to “Specification for Round 100mm Polished Monocrystalline Gallium Arsenide Wafers
- Doc. 6818, Withdrawal of SEMI M9.1-0813 — Specification For Round 50.8 mm Polished Monocrystalline Gallium Arsenide Wafers For Electronic Device Applications
- Doc. 6819, Withdrawal of SEMI M9.6-0813 — Specification For Round 125 mm Diameter Polished Monocrystalline Gallium Arsenide Wafers

Task Force Updates



- M86 (GaN) Revision TF
 - Drafting Doc. 6806, Revision of M86, Specification for Polished Monocrystalline c-Plane Gallium Nitride Wafers (Subject: To revise 1-4 inches diameter)
 - Coordinating with Gallium Nitride manufacturers and end users

5 year review

- SEMI M65-0816, Specification for Sapphire Substrates to use for Compound Semiconductor Epitaxial Wafers
 - Checking with sapphire substrate manufacturers for input.

Thank You!

Staff Contact: Kevin Nguyen, SEMI HQ
knguyen@semi.org